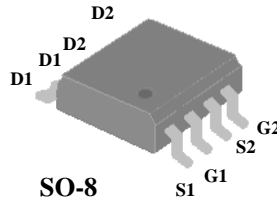


N-CANNEL ENHANCEMENT MODE POWER MOSFET

PRODUCT SUMMARY

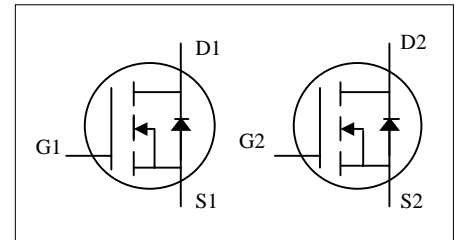
Low Gate Charge
Single Drive Requirement
Surface Mount Package



BV_{DSS}	80V
$R_{DS(ON)}$	90m Ω
I_D	3.5A

DESCRIPTION

The advanced power MOSFETs from Silicon Standard Corp. provide the designer with the best combination of fast switching, ruggedized device design, lower on-resistance and cost-effectiveness.



 **Pb-free; RoHS-compliant**

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage	± 25	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current ³ , $V_{GS} @ 10V$	3.5	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current ³ , $V_{GS} @ 10V$	2.8	A
I_{DM}	Pulsed Drain Current ¹	30	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	2	W
	Linear Derating Factor	0.016	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

THERMAL DATA

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient ³ Max.	62.5	$^\circ C/W$

ELECTRICAL CHARACTERISTICS @T_j=25°C(unless otherwise specified)

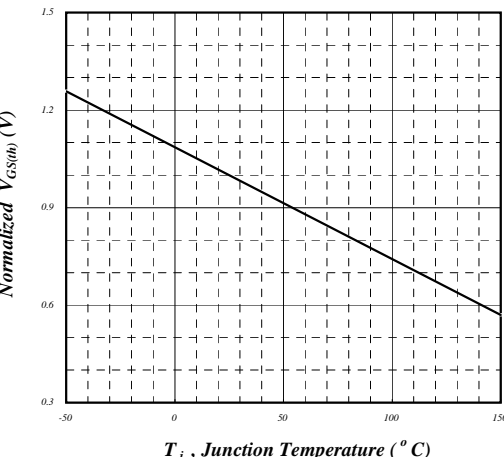
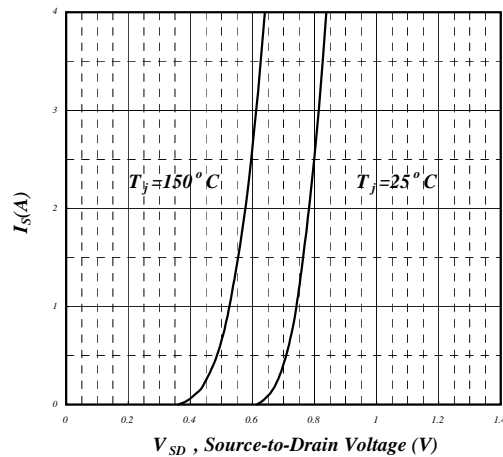
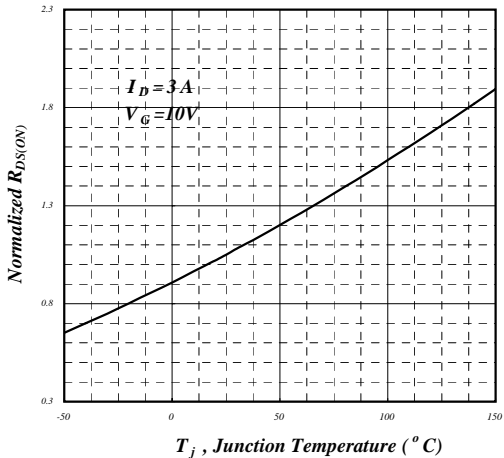
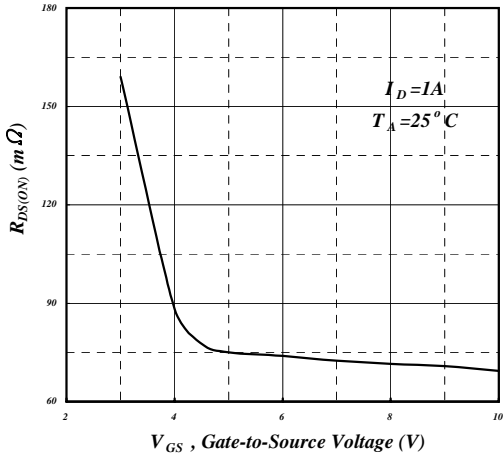
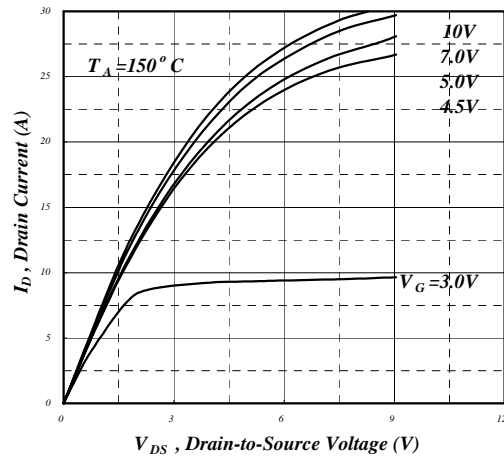
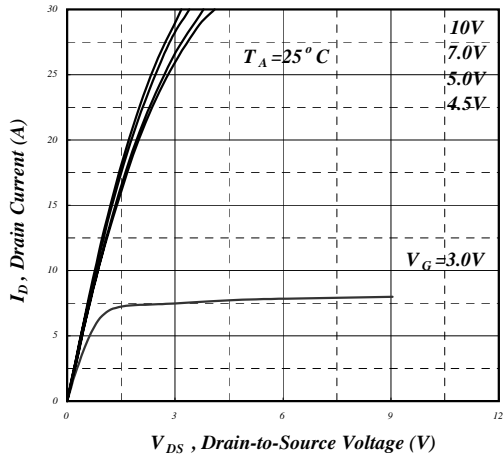
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =1mA	80	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =1mA	-	0.08	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =3A	-	-	90	mΩ
		V _{GS} =4.5V, I _D =1A	-	-	105	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	-	3	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =3A	-	7	-	S
I _{DSS}	Drain-Source Leakage Current (T _j =25°C)	V _{DS} =80V, V _{GS} =0V	-	-	1	uA
	Drain-Source Leakage Current (T _j =70°C)	V _{DS} =64V, V _{GS} =0V	-	-	25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±25V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =3A	-	11	18	nC
Q _{gs}	Gate-Source Charge	V _{DS} =64V	-	3	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	5	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =40V	-	8	-	ns
t _r	Rise Time	I _D =1A	-	4	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =10V	-	24	-	ns
t _f	Fall Time	R _D =40Ω	-	5	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	980	1570	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	70	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	50	-	pF
R _g	Gate Resistance	f=1.0MHz	-	1.2	1.8	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =1.6A, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time ²	I _S =3A, V _{GS} =0V,	-	30	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	40	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse width ≤300us , duty cycle ≤2%.
- 3.Surface mounted on 1 in² copper pad of FR4 board ; 135°C/W when mounted on min. copper pad.



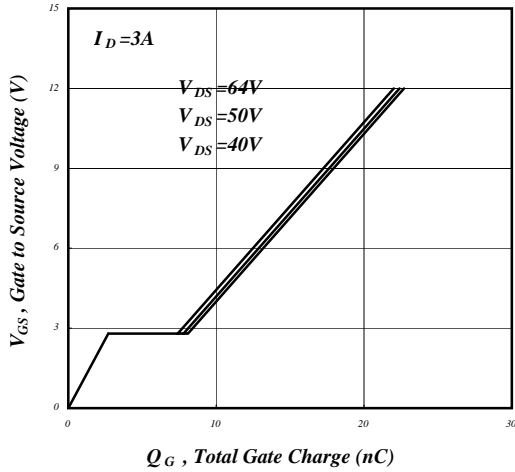


Fig 7. Gate Charge Characteristics

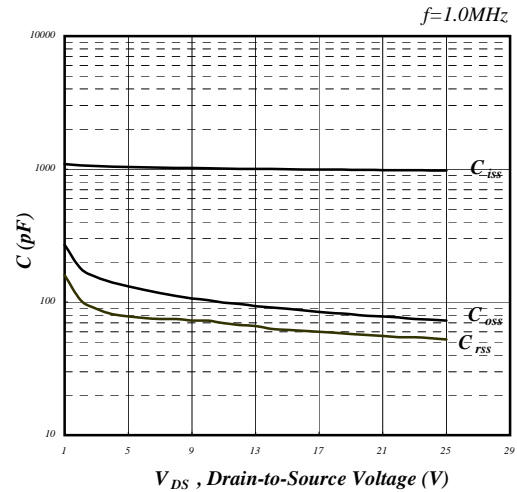


Fig 8. Typical Capacitance Characteristics

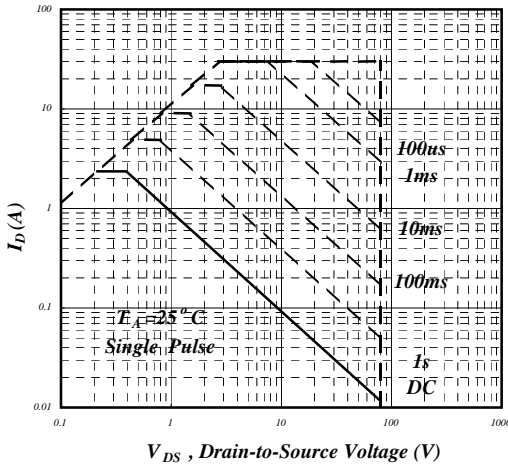


Fig 9. Maximum Safe Operating Area

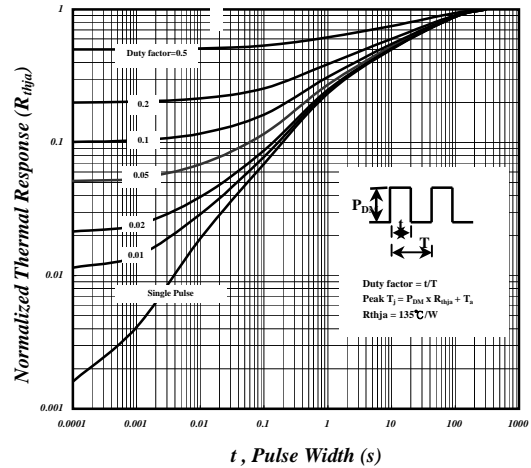


Fig 10. Effective Transient Thermal Impedance

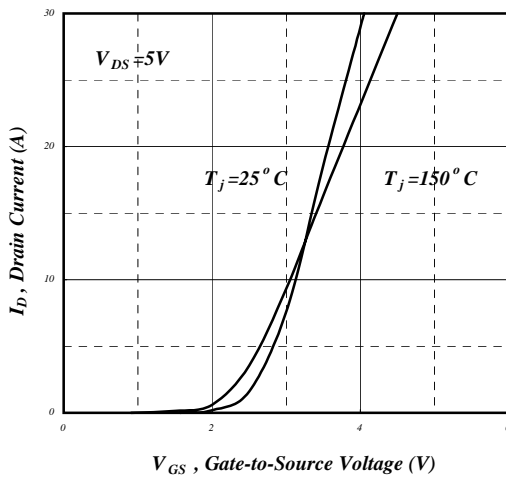


Fig 11. Transfer Characteristics

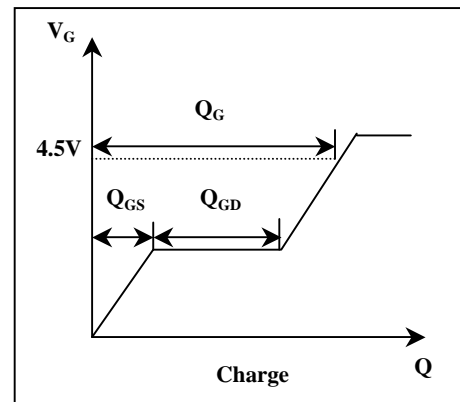


Fig 12. Gate Charge Waveform

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